

WHAT IS CLAIMED IS:

1. A method for processing photoresist, said method comprising steps of:
forming a layer of photoresist on a semiconductor structure;
defining a predetermined pattern on the photoresist;
removing unnecessary portions of the photoresist and maintaining necessary portions of the photoresist to form the predetermined pattern; and
performing compacting process to the left photoresist.
2. The method as claimed in Claim 1, wherein the compacting process comprises plasma process to make the photoresist dense.
3. The method as claimed in Claim 2, wherein the plasma process uses argon plasma.
4. A method for processing photoresist, said method comprising steps of:
forming a layer of photoresist on a semiconductor structure;
performing compacting process to the photoresist; and
forming the photoresist with a predetermined pattern.
5. The method as claimed in Claim 4, wherein the compacting process comprises plasma process to make the photoresist dense.
6. The method as claimed in Claim 5, wherein the plasma process uses argon plasma.